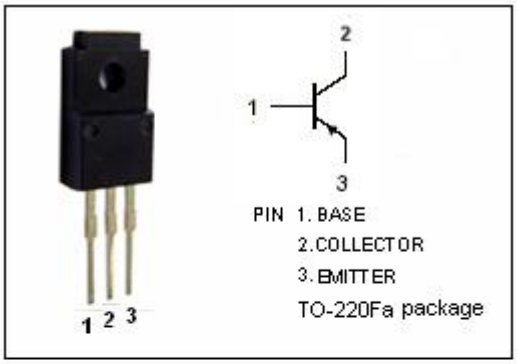
isc Silicon PNP Power Transistor — 2SA1279



DESCRIPTION

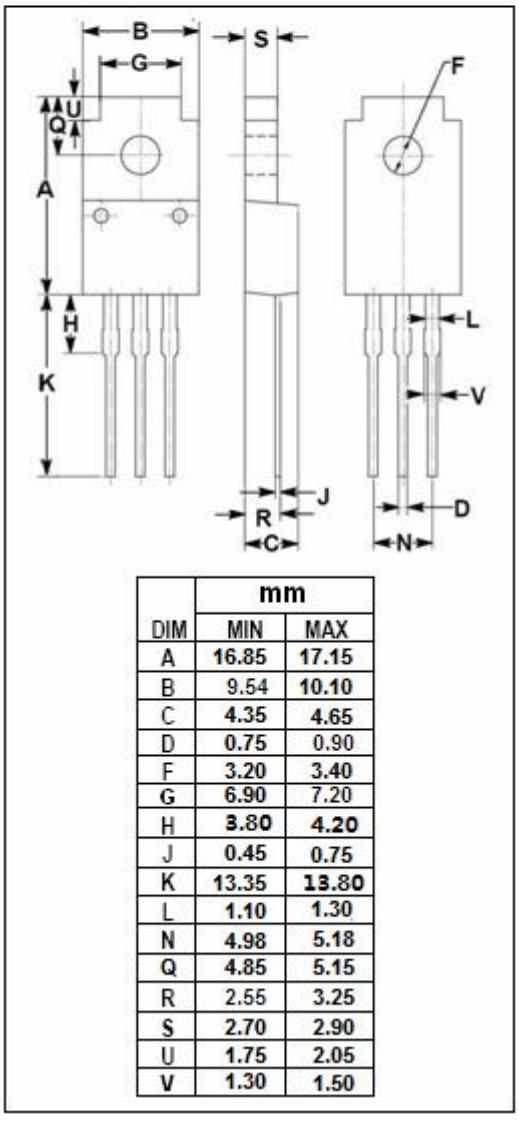
- Collector-Emitter Breakdown Voltage
  : $V_{(BR)CEO}$= -60V(Min)
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for high current switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-5	A
Icm	Emitter Current-pulse	-8	A
P_C	Total Power Dissipation @ T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	3.80	4.20
J	0.45	0.75
K	13.35	13.80
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA ; I_B= 0	-60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.15A			-0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -3A; I_B= -0.15A			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0			-1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -7V; I_C= 0			-1.0	μA
h_{FE-1}	DC Current Gain	I_C= -1.0A; V_{CE}= -1V	70		240	
h_{FE-2}	DC Current Gain	I_C= -3.0A; V_{CE}= -1V	30			
f_T	Current-Gain—Bandwidth Product	I_C= -1.0A;V_{CE}= -4V		60		MHz
C_{OB}	Output Capacitance	I_E=0; V_{CB}= -10V; f_{test}= 1.0MHz		200		pF